Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD package: 1.0 x 0.6 x 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-410	mA
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -410 \text{ mA}; T_j = 25 \text{ °C}$		-	1.2	1.4	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package	kage					
	Name	Description	Version				
PMZ1200UPE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883				

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ1200UPE	ZL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-410	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-260	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-1.7	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1670	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode		'		'	
Is	source current	T _{amb} = 25 °C	[1]	-	-410	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

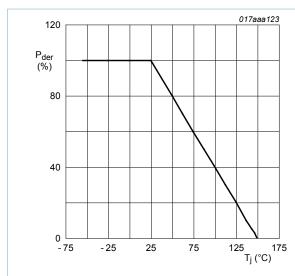


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

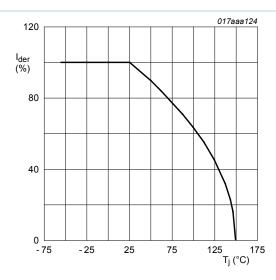


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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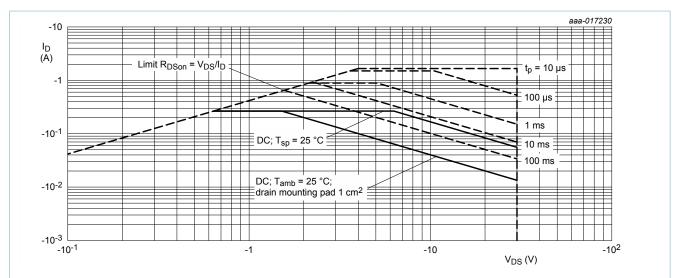


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from jur	thermal resistance		[1]	-	350	405	K/W
	from junction to ambient		<u>[2]</u>	-	270	310	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

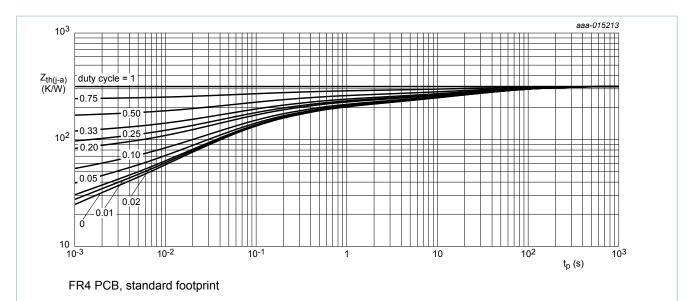
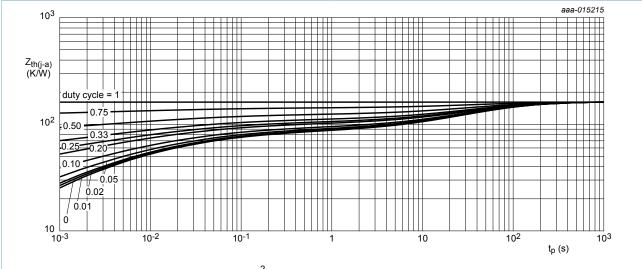


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -410 mA; T_j = 25 °C	-	1.2	1.4	Ω
resistar	resistance	V_{GS} = -4.5 V; I_D = -410 mA; T_j = 150 °C	-	2	2.4	Ω
		V_{GS} = -2.5 V; I_D = -320 mA; T_j = 25 °C	-	1.7	2.3	Ω
		V_{GS} = -1.8 V; I_{D} = -80 mA; T_{j} = 25 °C	-	2.1	3.1	Ω
		V_{GS} = -1.5 V; I_D = -10 mA; T_j = 25 °C	-	3	5.1	Ω
9fs	forward transconductance	V_{DS} = -10 V; I_D = -410 mA; T_j = 25 °C	-	820	-	mS
Dynamic c	haracteristics		'			
Q _{G(tot)}	total gate charge	$V_{DS} = -15 \text{ V}; I_D = -410 \text{ mA};$	-	0.7	1.2	nC
Q_{GS}	gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	43.2	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5.9	-	pF
C _{rss}	reverse transfer capacitance		-	4.2	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -15 V; I _D = -410 mA;	-	3	-	ns
t _r	rise time	$V_{GS} = -4.5 \text{ V}; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	14	-	ns
t _f	fall time		-	5	-	ns
Source-dra	ain diode		<u> </u>			
V_{SD}	source-drain voltage	I_S = -410 mA; V_{GS} = 0 V; T_i = 25 °C	_	-0.95	-1.2	V

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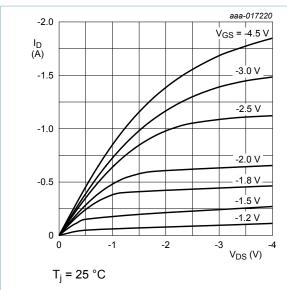
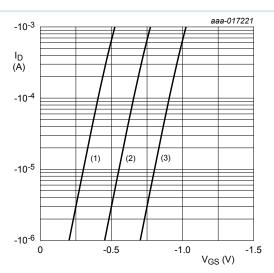


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 V_{DS} = -5 V

T_j = 25 °C

(1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

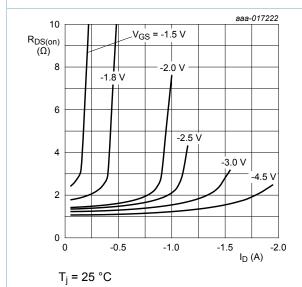


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

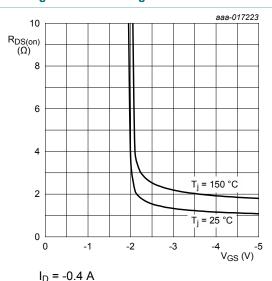


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

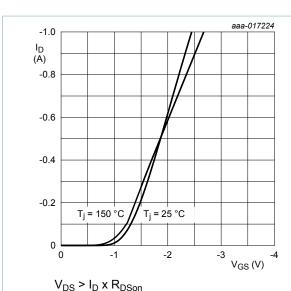


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

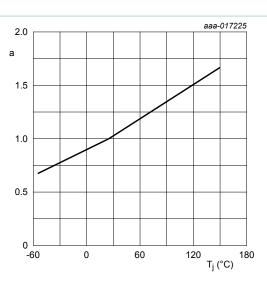
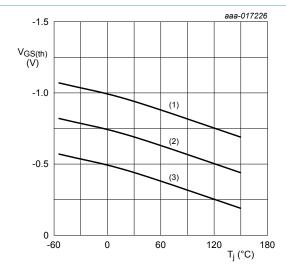


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

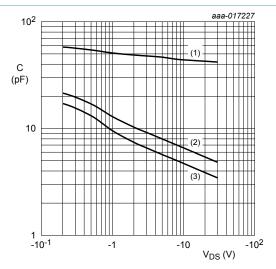
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = -250 \mu A; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

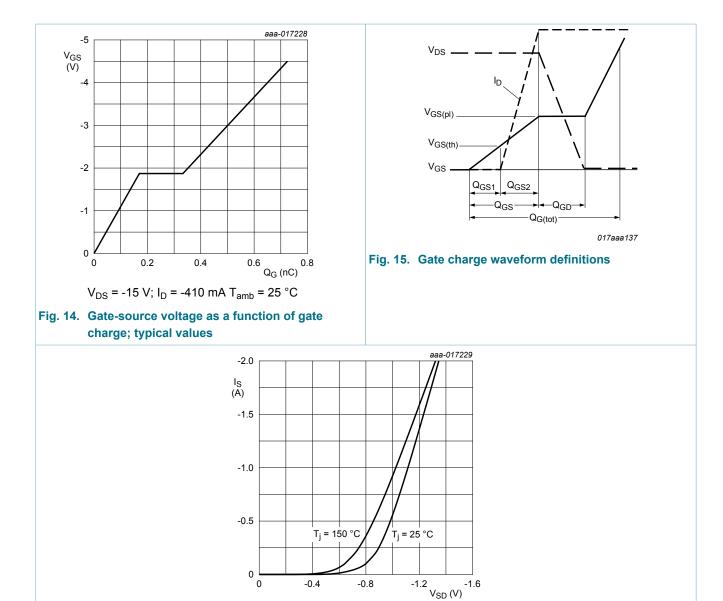


 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

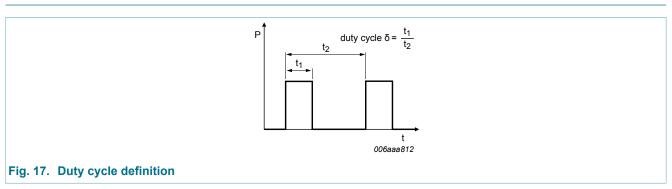
Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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11. Test information

 $V_{GS} = 0 V$



-0.8

Fig. 16. Source current as a function of source-drain voltage; typical values

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12. Package outline

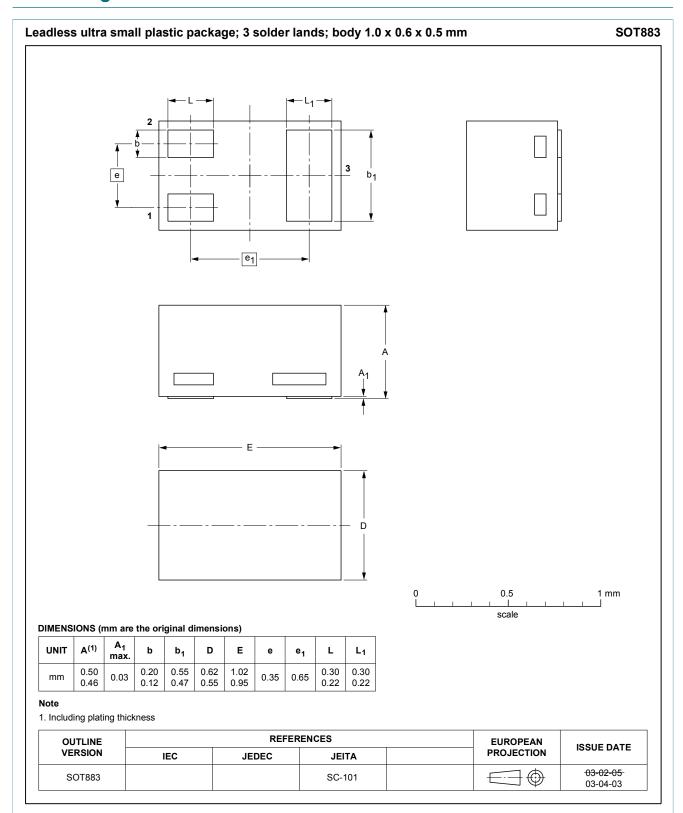
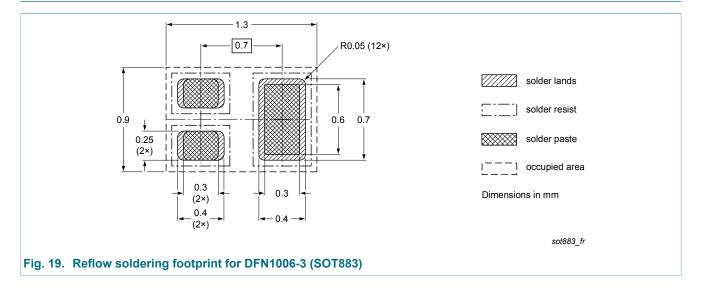


Fig. 18. Package outline DFN1006-3 (SOT883)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ1200UPE v.1	20150325	Product data sheet	-	-

15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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